Jun'ichi Kanasaki

List of Publications by Year
in descending order

33	547	687363 13	642732 23
papers	citations	h-index	g-index

33	33	33	597
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Formation of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>s</mml:mi><mml:msup><mml:mi>p</mml:mi><mml:mn>3</mml:mn></mml:msup></mml:math>-Bonded Carbon Nanostructures by Femtosecond Laser Excitation of Graphite. Physical Review Letters, 2009, 102, 087402.	7.8	132
2	Ultrafast relaxation of highly excited hot electrons in Si: Roles of the<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi mathvariant="normal">L</mml:mi><mml:mo>â^'</mml:mo><mml:mi mathvariant="normal">X</mml:mi></mml:mrow></mml:math>intervalley scattering. Physical Review B, 2011, 84, .	3.2	38
3	Primary Processes of Laser-Induced Selective Dimer-Layer Removal onSi(001)â^'(2Ã—1). Physical Review Letters, 2002, 89, 257601.	7.8	37
4	Imaging Energy-, Momentum-, and Time-Resolved Distributions of Photoinjected Hot Electrons in GaAs. Physical Review Letters, 2014, 113, 237401.	7.8	37
5	Formation of hot-electron ensembles quasiequilibrated in momentum space by ultrafast momentum scattering of highly excited hot electrons photoinjected into the Î“ valley of GaAs. Physical Review B, 2016, 93, .	3.2	37
6	Laser-induced bond breaking of the adatoms of the Si(111)-7 Ã— 7 surface. Surface Science, 1996, 349, L153-L158.	1.9	25
7	Ultrafast scattering processes of hot electrons in InSb studied by time- and angle-resolved photoemission spectroscopy. Physical Review B, 2015, 91, .	3.2	25
8	Site-sensitive yield of atomic emission induced by laser irradiation on Si(111)â^'7Ã—7 surface. Solid State Communications, 1996, 98, 913-916.	1.9	22
9	Laser-Induced Electronic Emissions of Si Atoms from Si(100) Surfaces. Japanese Journal of Applied Physics, 1993, 32, L859-L862.	1.5	19
10	Role of applied bias and tip electronic structure in the scanning tunneling microscopy imaging of highly oriented pyrolytic graphite. Physical Review B, 2012, 85, .	3.2	18
11	Photoinduced Structural Instability of the InP(110)â^'(1Ã—1)Surface. Physical Review Letters, 2004, 93, 117401.	7.8	17
12	Laser-induced electronic desorption from InP surfaces studied by femtosecond nonresonant ionization spectroscopy. Physical Review B, 2001, 64, .	3.2	16
13	Energy relaxation mechanism of hot-electron ensembles in GaAs: Theoretical and experimental study of its temperature dependence. Physical Review B, 2018, 97, .	3.2	16
14	Laser-induced electronic desorption of Si atoms fromSi(111)â^'(7Ã—7). Physical Review B, 2002, 66, .	3.2	13
15	Ultrafast relaxation dynamics of highly excited hot electrons in silicon. Physical Review B, 2019, 100, .	3.2	13
16	Defect initiated particle emission from semiconductor surfaces by laser irradiation. Surface Science, 1993, 283, 169-176.	1.9	11
17	Two-hole localization mechanism for electronic bond rupture of surface atoms by laser-induced valence excitation of semiconductors. Physical Review B, 2006, 74, .	3.2	11
18	Fermi-level dependent morphology in photoinduced bond breaking on (110) surfaces of IIIâ€“V semiconductors. Surface Science, 2007, 601, 2367-2372.	1.9	9

#	Article	IF	Citations
19	Ultrafast relaxation of photoinjected nonthermal electrons in the Î“ valley of GaAs studied by time- and angle-resolved photoemission spectroscopy. Physical Review B, 2021, 104, .	3.2	8
20	The DIET from semiconductor surfaces by excitation of valence electrons. Nuclear Instruments & Methods in Physics Research B, 1995, 101, 93-102.	1.4	7
21	Defect-initiated atomic emissions from semiconductor surfaces induced by laser irradiation: electronic cleaning of defects on surfaces. Applied Surface Science, 1994, 79-80, 100-103.	6.1	6
22	Ultrafast dynamics in photoexcited valence-band states of Si studied by time- and angle-resolved photoemission spectroscopy of bulk direct transitions. Physical Review B, 2018, 97, .	3.2	6
23	Intact-sheet double-layer ablation induced by femtosecond-laser excitation of graphite. Surface Science, 2011, 605, 1497-1502.	1.9	4
24	Low energy laser photoelectron study of defect states on cleaved Si(111)2 Ã— 1 surfaces. Surface Science, 1996, 349, L107-L110.	1.9	3
25	Photon energy dependence of the laser-induced emission yield of Si atoms from the Si(100) surface. Journal of Physics Condensed Matter, 1996, 8, 1475-1484.	1.8	3
26	<title>Laser-induced electronic bond breaking and structural changes on semiconductor surfaces</title>. , 1999, , .		3
27	Electronic bond rupture of Si atoms on Si()-(2Ã—1) induced by 1.16-eV photon excitation. Surface Science, 2003, 528, 115-120.	1.9	3
28	Comparison of Electronic-Excitation-Induced Structural Modification of Carbon-Based Nanomaterials with that of Semiconductor Surfaces. Nano, 2016, 11, 1630001.	1.0	2
29	Electronic structure of the surface unoccupied band of Ge(001)- <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>c</mml:mi><mml:mo>(</mml:mo><mml:mn>4</mml:mn><mml:mn>2</mml:mn><mml:mn>×</mml:mn><mml:mn>4</mml:mn><mml:mo>)</mml:mo></mml:mrow></mml:math> : Direct imaging of surface electron relaxation pathways. Physical Review B, 2017, 96, .	3.2	1
30	Enhancement of Emission of Si Atoms from Si(100) Surface by Low-Rate Br Exposure: A New Model of Dry Etching Based on Defect-Adsorbate Interaction. Japanese Journal of Applied Physics, 1994, 33, 2255-2257.	1.5	1
31	Laser-induced bond breaking and structural changes on Si(111)-7Ã—7 surfaces. Applied Surface Science, 1998, 127-129, 33-39.	6.1	1
32	<title>Laser-induced electronic desorption and structural changes on Si(001)-(2x1)</title>. , 2002, , .		1
33	Crucial roles of holes in electronic bond rupture on semiconductor surfaces. Surface Science, 2014, 626, 49-52.	1.9	1